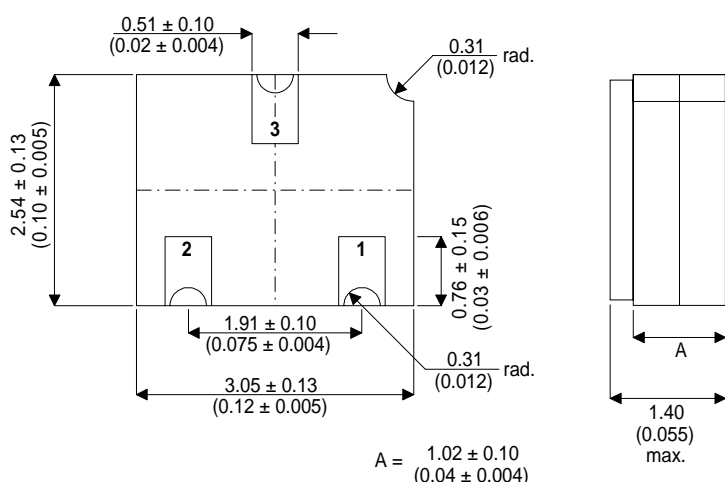


## MECHANICAL DATA

Dimensions in mm (inches)



## SILICON EPITAXIAL PLANAR DIODE

Fast Switching Diode in  
Hermetic Ceramic Surface Mount Package  
For High Reliability Applications

### SOT23 CERAMIC (LCC1 PACKAGE)

Underside View

PAD 1 — Anode    PAD 2 — Not Connected    PAD 3 — Cathode

## ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_R$	Reverse Voltage			75	V
$V_{RRM}$	Repetitive Peak Reverse Voltage			75	V
$I_{F(AV)}$	Average Rectified Forward Current			150	mA
$I_F$	Forward Current			200	mA
$I_{FRM}$	Repetitive Peak Forward Current			450	mA
$I_{FSM}$	Non-Repetitive Peak Forward Current	$t = 1\mu s$		2000	mA
		$t = 1s$		500	
$P_{tot}$	Power Dissipation at $T_{amb} = 25^{\circ}C$			500	mW

$T_{stg}$	Storage Temperature Range	-55 to +175 °C
$T_j$	Max junction temperature	+150°C

**CHARACTERISTICS** ( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$ Forward Voltage	$I_F = 10\text{mA}$			1	V
$I_R$ Reverse Current	$V_R = 20\text{V}$			25	nA
	$V_R = 20\text{V}, T_j = 150^{\circ}\text{C}$			50	$\mu\text{A}$
$V_{(BR)R}$ Reverse Avalanche Breakdown Voltage	$I_R = 100\mu\text{A}$	100			V
	$I_R = 5\mu\text{A}$	75			V
$C_d$ Capacitance	$V_R = 0\text{V}, f = 1\text{MHz}$			4	pF
$V_{fr}$ Forward Recovery Voltage	$I_F = 50\text{mA}, t_r = 20\text{ns}$			2.5	V
$t_{rr}$ Reverse Recovery Time	$I_F = 10\text{mA}$ to $I_R = 60\text{mA}$ $R_L = 100\Omega$			4	ns